

**IN THE SPECIFICATION:**

The specification as amended below with replacement paragraphs shows added text with underlining and deleted text with ~~strikethrough~~.

Please REPLACE paragraph [0026] with the following paragraph:

**[0026]** As shown in FIG. 2 and FIG. 3, the gas injector 2, disposed in an upper part of the chamber 1, comprises a supply pipe 21 supplying the reaction gas, and a gas supplier 22 including a first gas supply hole 221 and a second gas supply hole 222. A gas distributor plate 24 opposes the gas supplier 22 forming a gap therebetween. A showerhead 25 opposes the gas distributor plate 24, having a gap therebetween injecting the reaction gas into the chamber 1. After being sequentially layered, a first gap 30 is formed between the gas supplier 22 and the gas distributor plate 24 and a second gap 40 is formed between the gas distributor plate 24 and the showerhead 25.

Please REPLACE paragraph [0027] with the following paragraph:

**[0027]** Rf power 27 is applied from outside of the chamber 1 to form an electrode to form plasma inside the chamber. RF power is applied to the gas supplier 22 and the gas distributor plate 24 is used as an upper electrode. The support 3 is used as a bottom electrode.

Please REPLACE paragraph [0029] with the following paragraph:

**[0029]** In the gas distributor plate 24, a loop-type upper partition wall 26 protrudes from a central zone of an upper surface and a loop-type bottom partition wall 28 protrudes from a central zone of a bottom surface.

Please REPLACE paragraph [0030] with the following paragraph:

**[0030]** Thus, the first gap 30 formed between the gas supplier 22 and the gas distributor plate 24 is divided into the first central zone 31 and the first edge zone 32 by the upper partition wall, and the second gap 40 formed between the gas distributor plate 24 and the showerhead 25 is divided into a second central zone 41 and a second edge zone 42 by the bottom partition wall 28.

Please REPLACE paragraph [0031] with the following paragraph:

[0031] In the first central zone 31, a plurality of first gas distribution holes 51 are connected to the second central zone 41 passing through a plate of the gas distributor plate 24, and a plurality of second gas distribution holes 52 are connected to the second edge zone 42 passing through the plate of the gas distributor plate 24 in the first edge zone 32.

Please REPLACE paragraph [0032] with the following paragraph:

[0031] The gas distributor plate 24 may contain an aluminium alloy, and the showerhead 25 may contain silicon. In the above embodiment of the present invention, one gas distributor plate 24 is provided between the gas supplier 2422 and the showerhead 25, but a plurality of gas distributors plates 24 are alternatively layered as shown in FIG. 7.

Please REPLACE paragraph [0034] with the following paragraph:

[0034] The reaction gas passes through the first gas supplier 221 and the second gas supplier 222 of the gas supplier 22. The reaction gas is circulated in the first gap 30 formed between the gas supplier 22 and the gas distributor plate 24. The reaction gas passed through the first gas supply hole 221 flows into the first central zone 31 of the first gap 30, and the reaction gas passed through the second gas supply hole 222 flows to the first edge zone 32 of the first gap 30.

Please REPLACE paragraph [0035] with the following paragraph:

[0035] The reaction gas in the first gap 30 is divided between the first central zone 31 and the first edge zone 32. The reaction gas from the first central zone then flows into the second central zone 41 of the second gap 40 formed between the gas distributor plate 24 and the showerhead 25. The gas passes through the first gas supply hole 51 placed in the first central zone 31. The gas from the first edge zone 32 flows into the second edge zone 42 of the second gap 40 formed between the gas distributor plate 24 and the showerhead 25 and passes through the second gas supply hole 52 of the gas distributor plate 24 placed in the first edge zone 32.

Please REPLACE paragraph [0038] with the following paragraph:

[0038] With the upper partition wall 26 and the bottom partition wall 28 structure according to an aspect of the present invention, the gas distributor plate 24 can separately inject reaction gas to a central zone inside the chamber 1 through the plurality of first distribution holes 61, and an edge zone inside the chamber 1 through the plurality of second distribution holes 62. Therefore, the amount of the reaction gas supplied into the central zone and the edge zone of the chamber 1 can be independently controlled.

Please REPLACE paragraph [0040] with the following paragraph:

[0040] The increasing or decreasing of the amount of reaction gas in the central zone, the edge zone of the chamber 1, or one zone independently from the other zone, according to an aspect of the present invention, is possible because the reaction gas is divided, into the first central zone 31 and the first edge zone 32, and into the second central zone 41 and the second edge zone 42 by the upper partition wall 26 and the bottom partition wall 28, without being mixed while the reaction gas is passing through the gas distributor plate 24.

Please REPLACE paragraph [0041] with the following paragraph:

[0041] The etching apparatus according to an aspect of the present invention also includes an MFC (Mass Flow Controller)71. The amount of reaction gas supplied into the first central zone 31 formed between the gas supplier 22 and the gas distributor plate 24 is increased or decreased independently from the first edge zone 32, and the amount of reaction gas supplied into the first edge zone 32 is increased or decreased independently from the first central zone 31. The MFC 71 accurately controls the amount of various kinds of gas a user wants that are used for a semiconductor manufacturing.

Please REPLACE paragraph [0042] with the following paragraph:

[0042] In an MFC 71, a fluid is heated if a heating material is positioned in the path of the fluid flow. The temperature between an upper stream and a lower stream of the fluid for the heating material is initially different, but the heating material loses heat and cools down. A valve for the fluid is controlled by an electric signal generated after estimating a speed and amount of the fluid

by detecting the above change of the temperature. According to an aspect of the invention, the MFC includes a sensor, a control valve, a bypass, a base block, and an electric circuit.

Please REPLACE paragraph [0043] with the following paragraph:

**[0043]** As described above, the MFC is used to control a valve. According to an aspect of the present invention, the etching apparatus further comprises a control valve 73 automatically operated by a controller. Therefore, the amount of reaction gas supplied to the first central zone 31 and the first edge zone 32 respectively is controlled. The control valve 73 is automatically controlled by the control part or controlled manually.